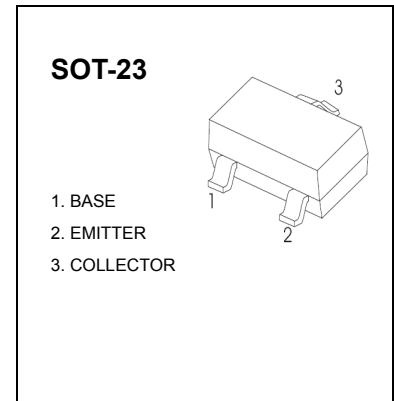


### SOT-23 Plastic-Encap sulate Transistors

#### FEATURES

- Ideally suited for automatic insertion
- For switching and AF amplifier applications



#### MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	TKBC846	80
		TKBC847	50
		TKBC848	30
V <sub>CEO</sub>	Collector-Emitter Voltage	TKBC846	65
		TKBC847	45
		TKBC848	30
V <sub>EBO</sub>	Emitter-Base Voltage	6	V
I <sub>C</sub>	Collector Current –Continuous	0.1	A
P <sub>C</sub>	Collector Power Dissipation	200	mW
R <sub>θJA</sub>	Thermal Resistance From Junction To Ambient	625	°C/W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55~+150	°C

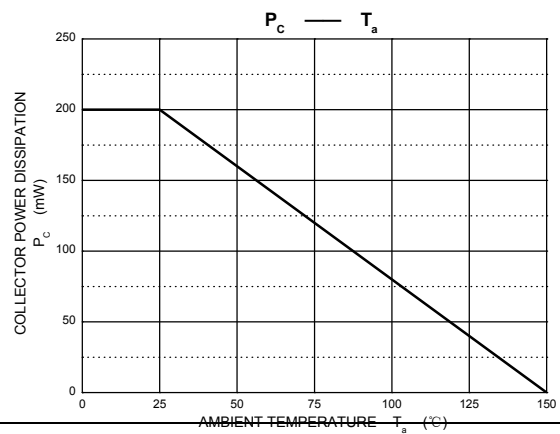
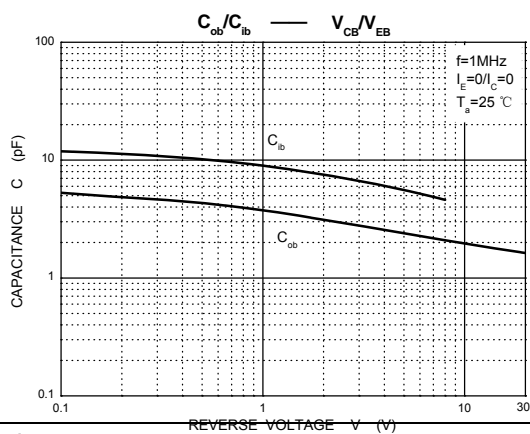
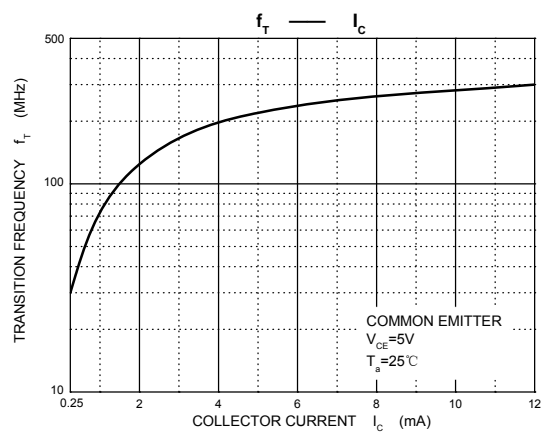
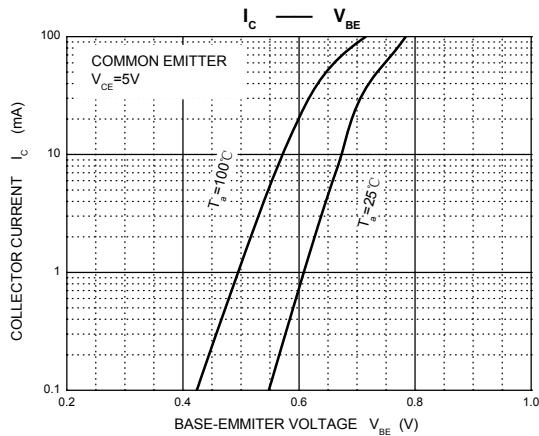
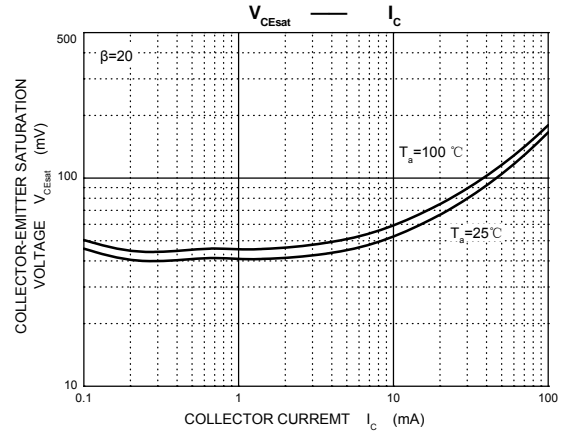
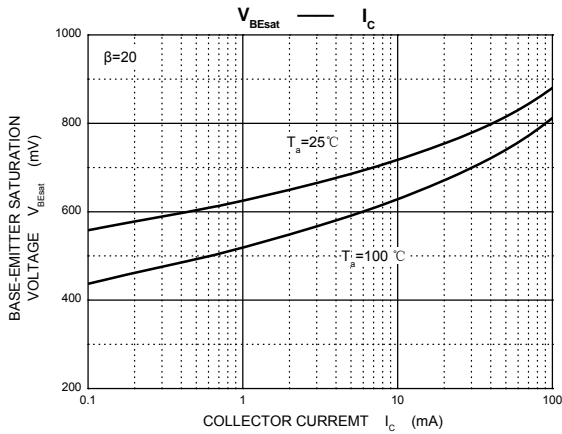
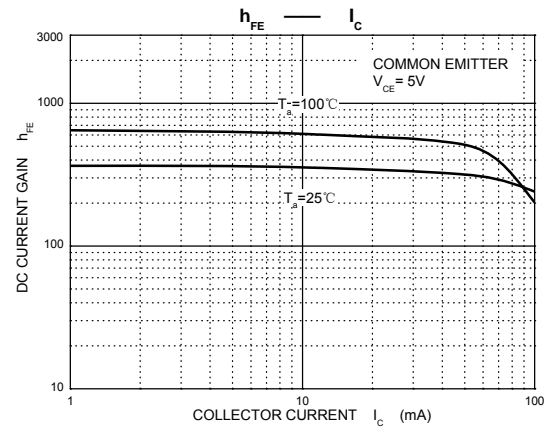
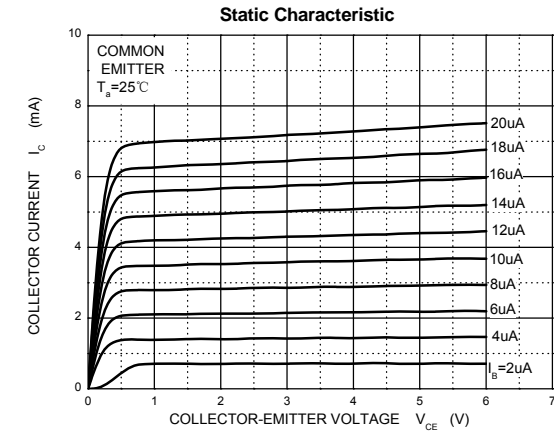
#### DEVICE MARKING

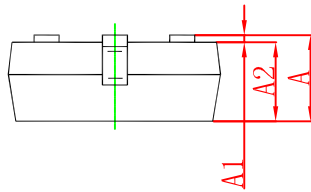
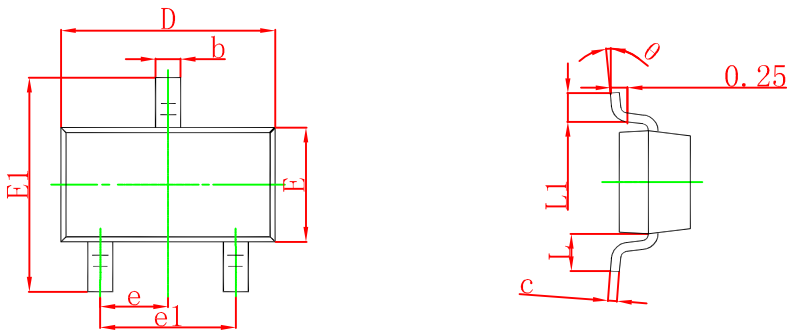
TKBC846A=1A; TKBC846B=1B;  
 TKBC847A=1E; TKBC847B=1F; TKBC847C=1G;  
 TKBC848A=1J; TKBC848B=1K; TKBC848C=1L

**ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit	
Collector-base breakdown voltage	TKBC846	I <sub>C</sub> = 10μA, I <sub>E</sub> =0	80			V	
	TKBC847		50				
	TKBC848		30				
Collector-emitter breakdown voltage	TKBC846	I <sub>C</sub> = 10mA, I <sub>B</sub> =0	65			V	
	TKBC847		45				
	TKBC848		30				
Emitter-base breakdown voltage	V <sub>EBO</sub>	I <sub>E</sub> = 10μA, I <sub>C</sub> =0	6			V	
Collector cut-off current	TKBC846	I <sub>CBO</sub>	V <sub>CB</sub> =70 V, I <sub>E</sub> =0			0.1	μA
	TKBC847		V <sub>CB</sub> =50 V, I <sub>E</sub> =0				
	TKBC848		V <sub>CB</sub> =30 V, I <sub>E</sub> =0				
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =5 V, I <sub>C</sub> =0			0.1	μA	
DC current gain	TKBC846A,847A,848A	h <sub>FE</sub>	V <sub>CE</sub> = 5V, I <sub>C</sub> = 2mA	110		220	
	TKBC846B,847B,848B			200		450	
	TKBC847C,TKBC848C			420		800	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =100mA, I <sub>B</sub> = 5mA			0.5	V	
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =100mA, I <sub>B</sub> = 5mA			1.1	V	
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = 5 V, I <sub>C</sub> = 10mA f=100MHz	100			MHz	
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V,f=1MHz			4.5	pF	

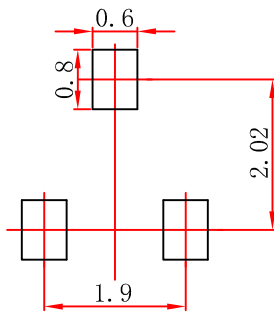
## Typical Characteristics





Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

### SOT-23 Suggested Pad Layout



- Note:
1. Controlling dimension: in millimeters.
  2. General tolerance:  $\pm 0.05$  mm.
  3. The pad layout is for reference purposes only.